

SANYO	No.5297A	2SJ383
		P-Channel MOS Silicon FET

Ultrahigh-Speed Switching Applications

Features

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

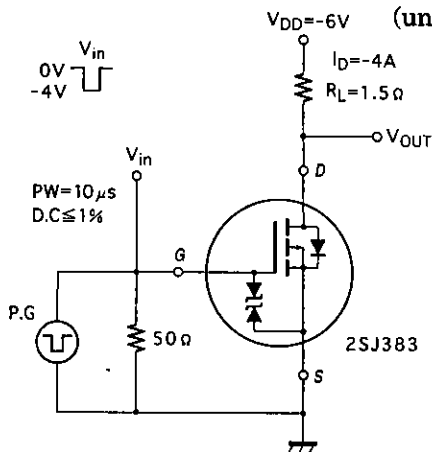
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V_{DSS}	-12	V
Gate-to-Source Voltage	V_{GSS}	±10	V
Drain Current (DC)	I_D	-8	A
Drain Current (Pulse)	I_{DP}	-32	A
Allowable Power Dissipation	P_D	1.0	W
		$T_c = 25^\circ\text{C}$	
		30	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

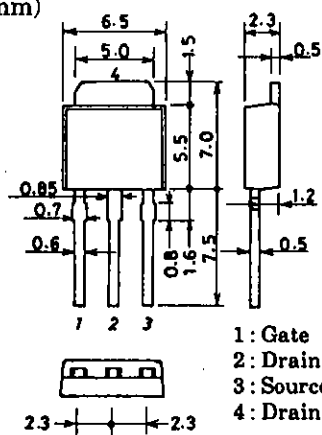
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -10\text{V}, V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8\text{V}, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -6\text{V}, I_D = -1\text{mA}$	-0.4		-1.4	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -6\text{V}, I_D = -4\text{A}$	6	8		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -4\text{A}, V_{GS} = -4\text{V}$		65	82	mΩ
	$R_{DS(on)}$	$I_D = -2\text{A}, V_{GS} = -2.5\text{V}$		90	144	mΩ
Input Capacitance	C_{iss}	$V_{DS} = -6\text{V}, f = 1\text{MHz}$		1000		pF
Output Capacitance	C_{oss}	$V_{DS} = -6\text{V}, f = 1\text{MHz}$		800		pF
Reverse Transfer Capacitance	C_{res}	$V_{DS} = -6\text{V}, f = 1\text{MHz}$		270		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		25		ns
Rise Time	t_r	"		170		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		180		ns
Fall Time	t_f	"		270		ns
Diode Forward Voltage	V_{SD}	$I_S = -8\text{A}, V_{GS} = 0$	-1.0	-1.2		V

Switching Time Test Circuit



Package Dimensions 2083B

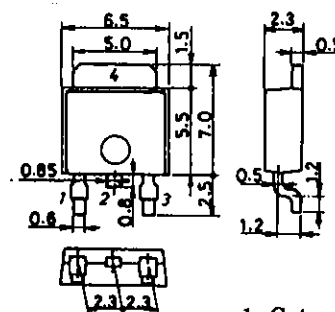
(unit: mm)



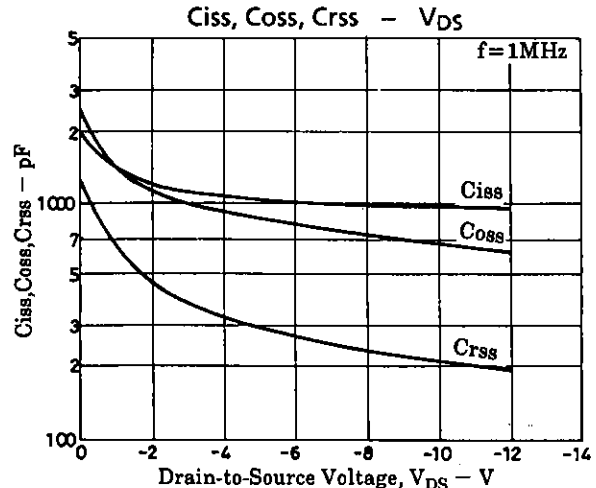
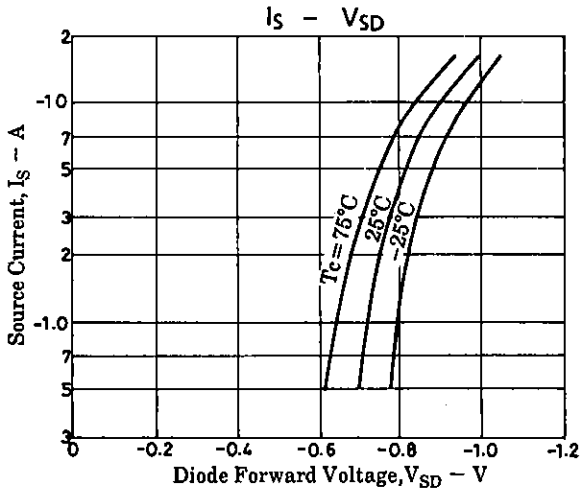
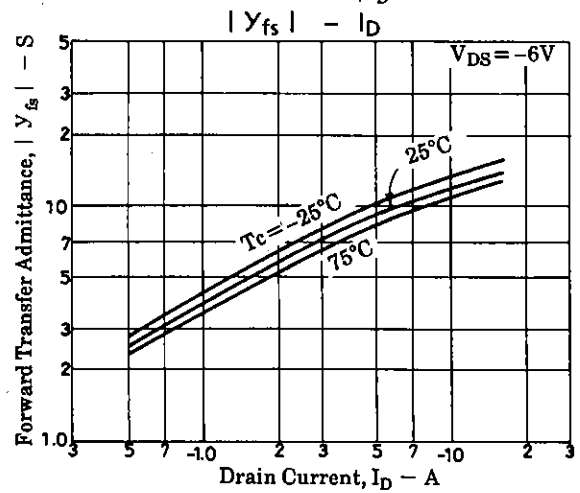
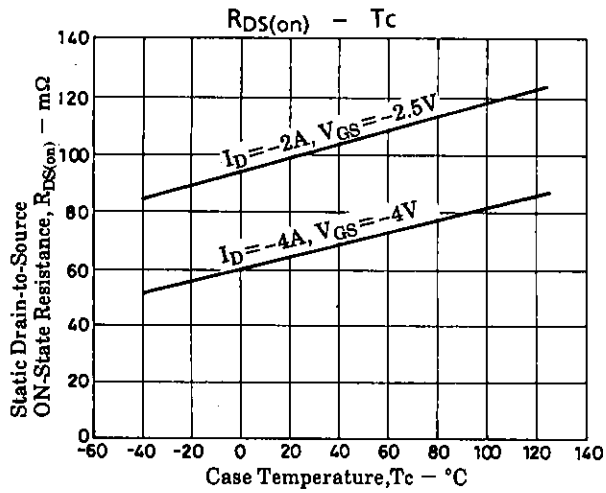
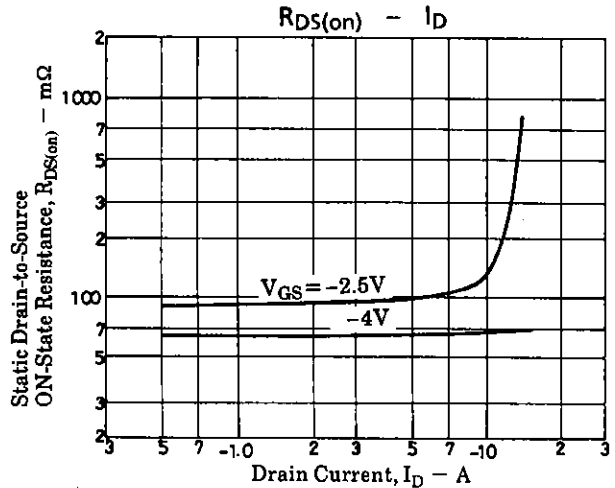
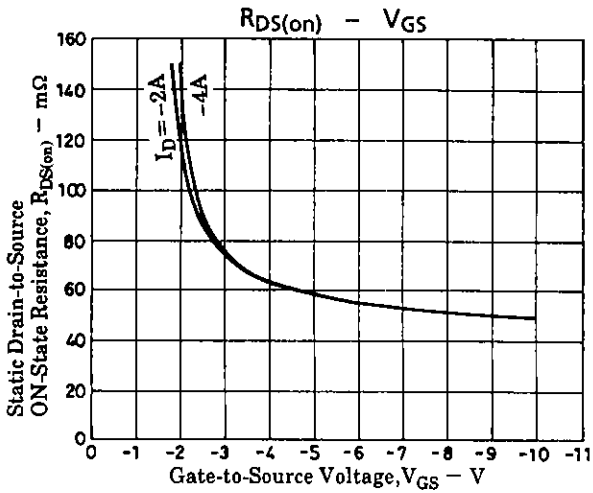
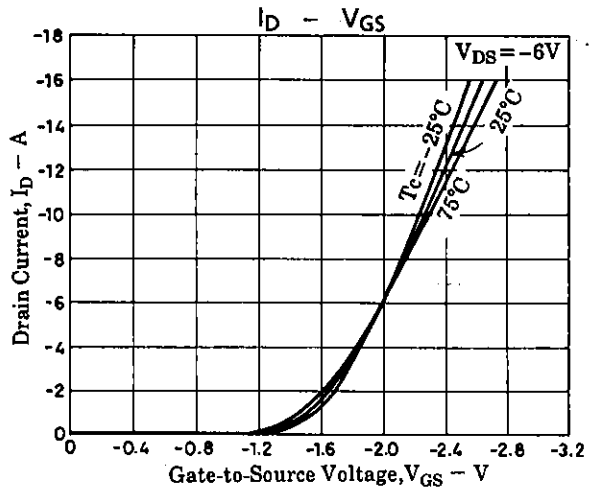
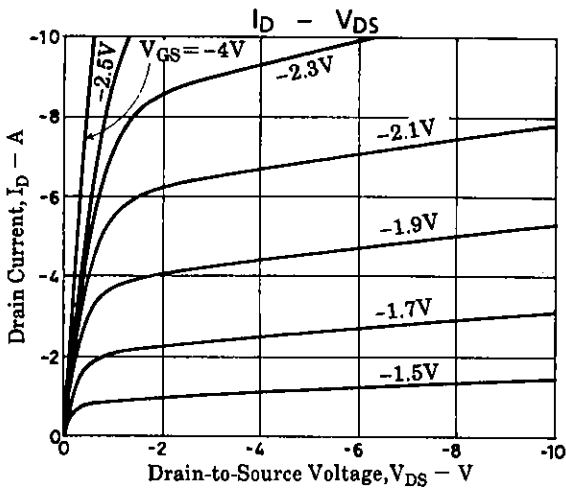
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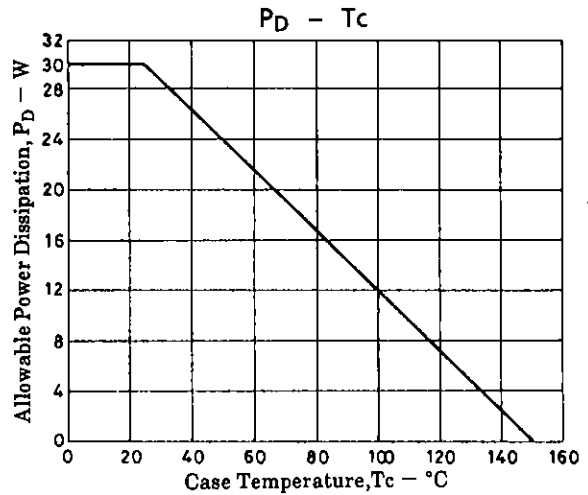
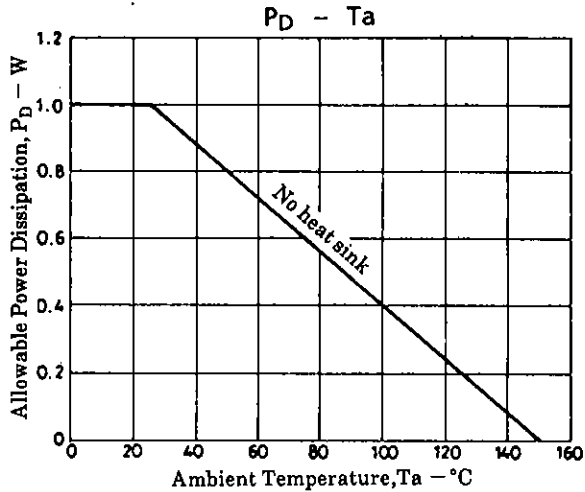
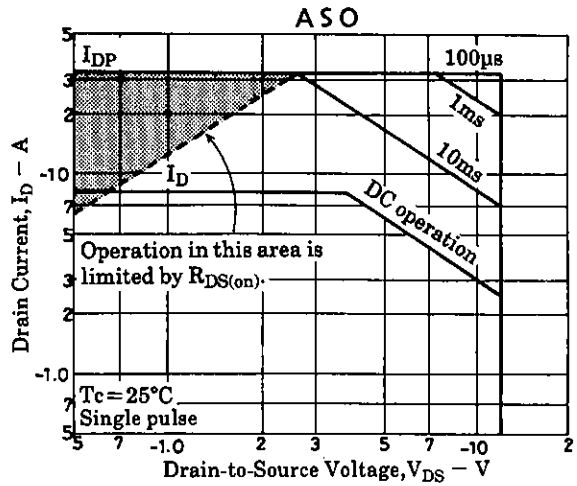
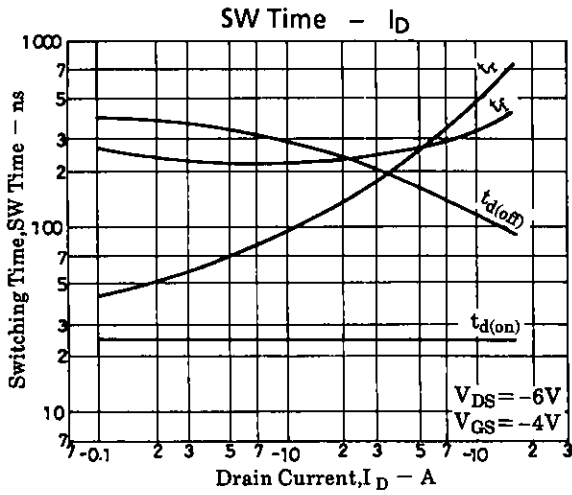
Package Dimensions 2092B

(unit: mm)



SANYO: TP-FA





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